

Hall effect switch sensor

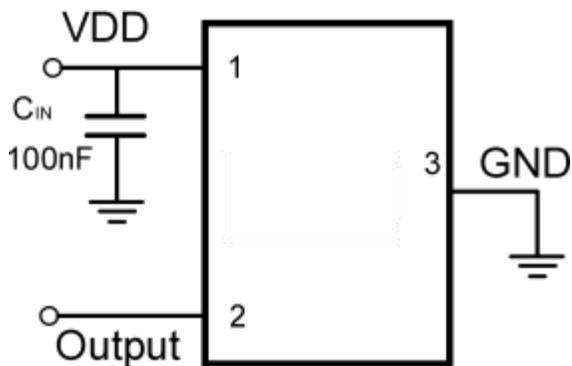
1. Features

- Low power consumption
 - 5Hz version: 1.6uA@ 1.8V
 - 20Hz version: 3.3uA@ 1.8V
- Wide operating voltage range: 1.6V~5.5V
- Selectable magnetic field threshold (B_{op})
 - 33Gs Low Threshold
 - 46Gs High Threshold
- Single S-pole magnetic field detection
- CMOS Push-pull output
- Package: SOT-23
- Operating temperature range: -40°C~85°C
- Excellent ESD performance: HBM 8KV
- RoHS compliant

2. Typical Applications

- Laptop and Tablet Switch Detection
- TWS earphones, mobile phones
- Electronic lock, valve position detection
- Water meter, gas meter, flow meter
- Non-contact detection

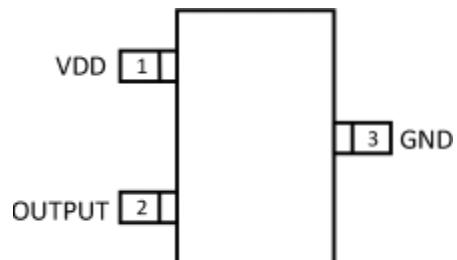
3. Application Circuit Schematic



Note: In order to filter out the noise at the power supply end of the chip, a 100nF capacitor should be connected between the power supply and the ground, and the capacitor should be as close to the VDD pin as possible.

5. Pin definition and marking information

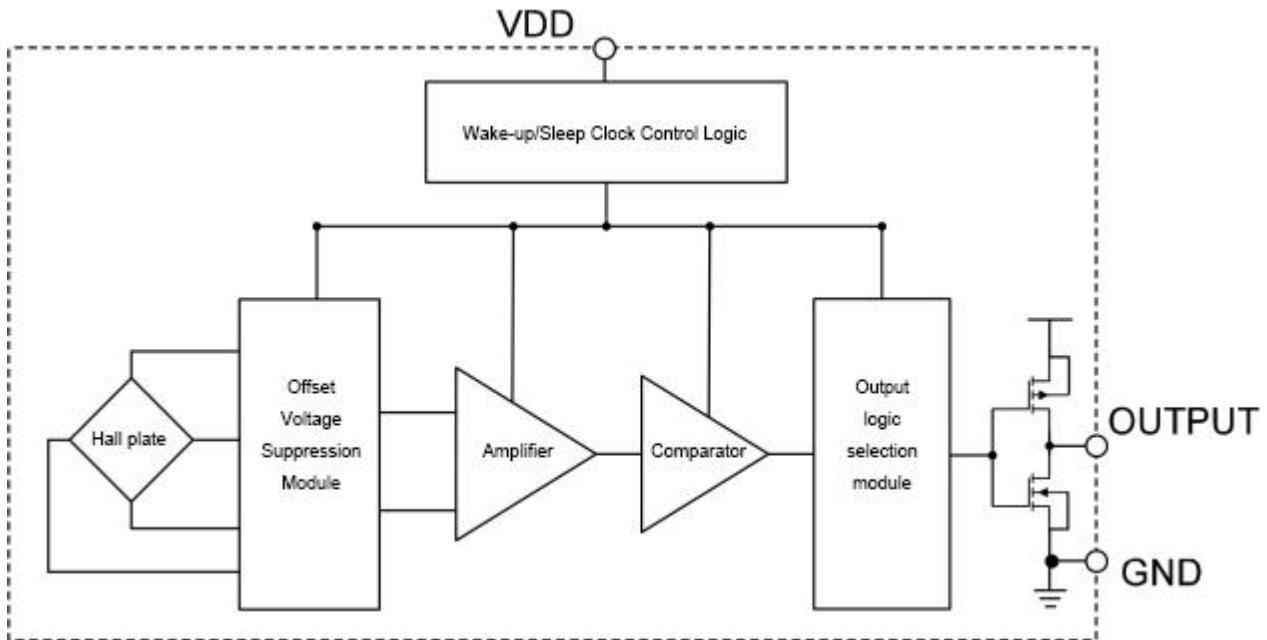
SOT-23



Pin structure (top view)

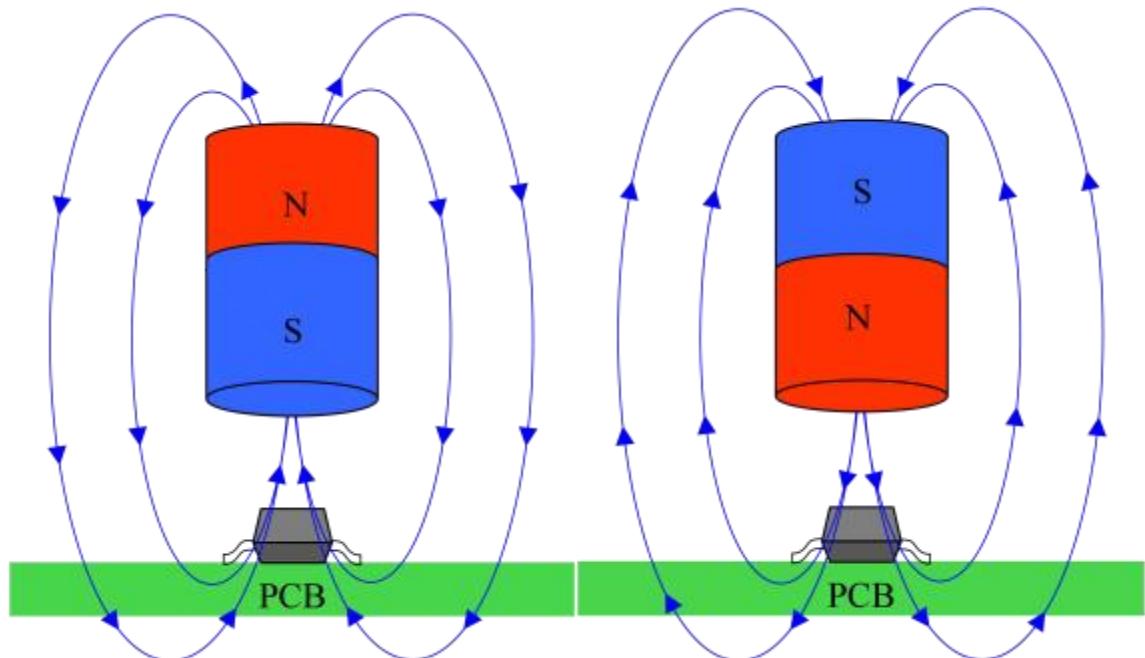
Pin Name	Pin Number	Functional Description
VDD	1	Power input
OUTPUT	2	Power output
GND	3	Ground

6.Function Diagram

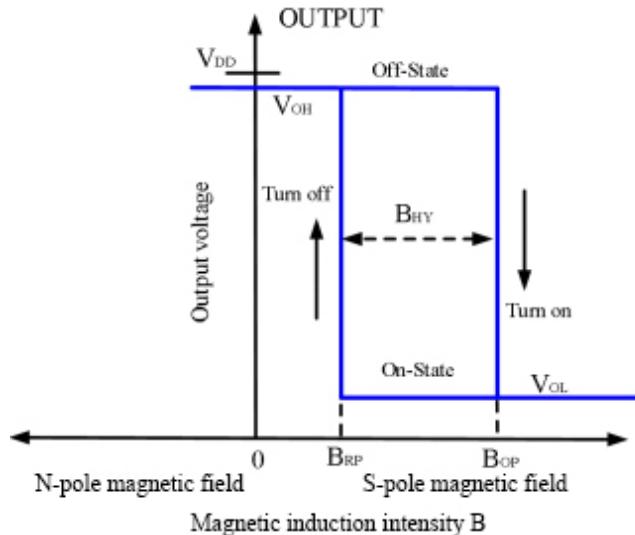


7.Switching output characteristics

As shown in the figure below, when the south pole of the magnet is close to the top of the chip, the magnetic flux lines pass from the bottom to the top of the chip, and the magnetic induction intensity B is considered to be positive at this time; when the north pole of the magnet is close to the top of the chip, the magnetic flux lines pass from the top to the bottom of the chip, and the magnetic induction intensity B is considered to be negative at this time.

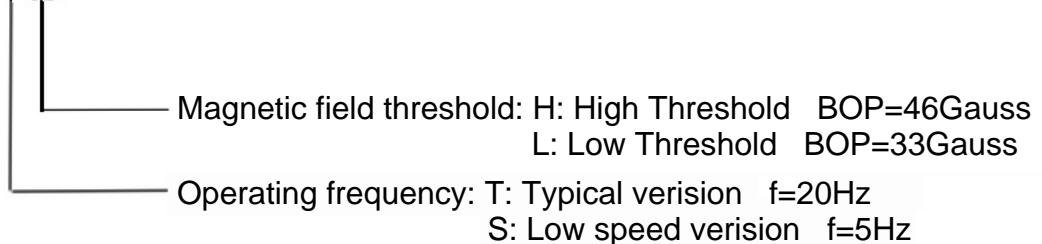


Output Characteristics



8. Product model composition

SL 1613 - X X



9. Absolute Maximum Ratings (@TA=+25°C, Unless otherwise specified)

Project	Parameter description	Value	Unit
V _{DD}	Supply voltage	6	V
V _{DD_REV}	Reverse supply voltage	-0.3	V
I _{OUTPUT}	Output drive current	5	mA
B	Magnetic induction intensity	No limit	Gauss
P _D	Package	400	mW
T _{STG}	Operating temperature range	-50~+150	oC
T _J	Maximum temperature resistance of the node	150	oC
ESD HBM	Human Body Model ESD Capability	8000	V

Note: Stresses exceeding the absolute maximum ratings may cause permanent damage. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

10. Reference working conditions (@TA=+25°C, Unless otherwise specified)

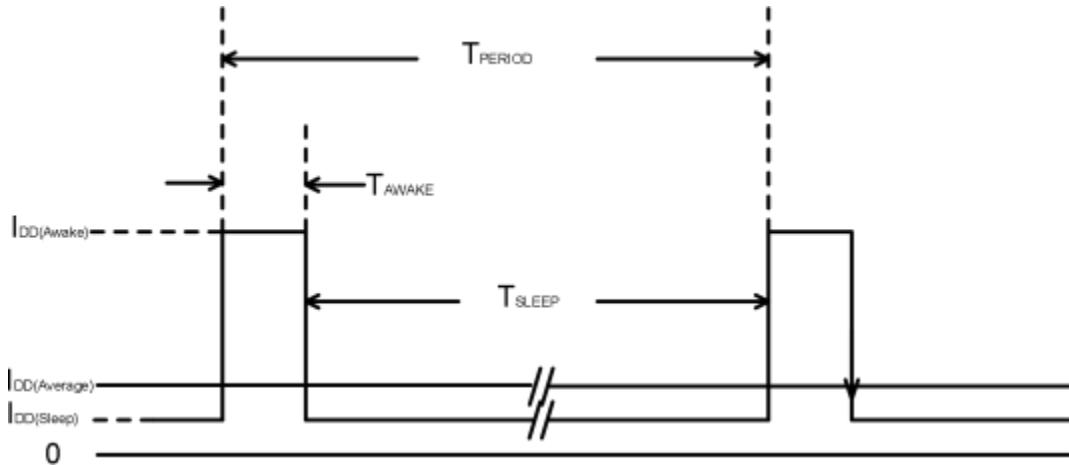
Project	Parameter description	Working conditions	Value	Unit
VDD	Supply voltage range	Chip working	1.6~5.5	V
TA	Operating temperature range	Chip working	-40~85	oC

11. Electrical parameters (@TA=+25°C, VDD=1.8V Unless otherwise specified)

SL 1613-TX Series						
Project	Parameter description	Working conditions	Min	Typ	Max	Unit
V _{DD}	Supply voltage	Working status	1.6	—	5.5	V
V _{OL}	Output low level	I _{OUT} = 1mA	—	0.02	0.1	V
V _{OH}	Output high level	I _{OUT} = 1mA	VDD-0.1	VDD-0.02	—	V
I _{DD(AVG)}	Average current	TA=+25°C , VDD= 1.8V	—	3.3	—	µA
I _{DD(Awake)}	Wake-up state current	TA=+25°C , VDD= 1.8V	—	2	—	mA
I _{DD(Sleep)}	Sleep state current	TA=+25°C , VDD= 1.8V	—	1	—	µA
T _{AWAKE}	Wake-up time	Working status	—	50	—	µs
T _{PERIOD}	Cycle	Working status	—	50	—	ms

SL1613-SX Series						
Project	Parameter description	Working conditions	Min	Typ	Max	Unit
V _{DD}	Supply voltage	Working status	1.6	—	5.5	V
V _{OL}	Output low level	I _{OUT} = 1mA	—	0.02	0.1	V
V _{OH}	Output high level	I _{OUT} = 1mA	V _{DD} -0.1	V _{DD} -0.02	—	V
I _{DD(AVG)}	Average current	TA=+25°C , V _{DD} = 1.8V	—	1.6	—	µA
I _{DD(Awake)}	Wake-up state current	TA=+25°C , V _{DD} = 1.8V	—	2	—	mA
I _{DD(Sleep)}	Sleep state current	TA=+25°C , V _{DD} = 1.8V	—	1	—	µA
T _{AWAKE}	Wake-up time	Working status	—	50	—	µs
T _{PERIOD}	Cycle	Working status	—	200	—	ms

Note: After the chip is powered on (VDD is 1.6V~5.5V), the output starts sampling and output state is valid after second working cycle.



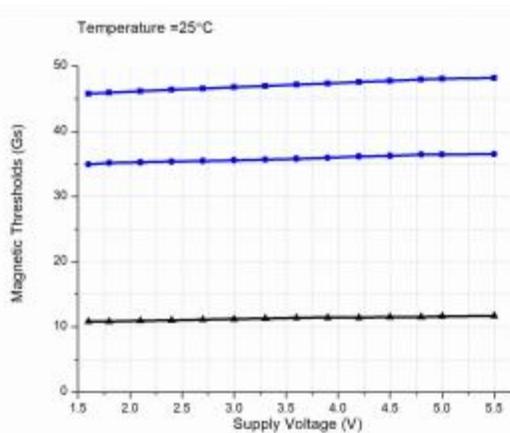
12. Magnetic parameters (@TA=+25°C, VDD=1.8V Unless otherwise specified)

Project	Parameter description	Working conditions	Min	Typ	Max	Unit
SL1613-XL Series						
B _{OPS}	Magnetic field operating point	TA=+25°C , VDD= 1.8V	26	33	38	Gauss
B _{RPS}	Magnetic field release point	TA=+25°C , VDD= 1.8V	16	23	28	
B _{HY} (B _{OPS} - B _{RPS})	Hysteresis		-	10	-	

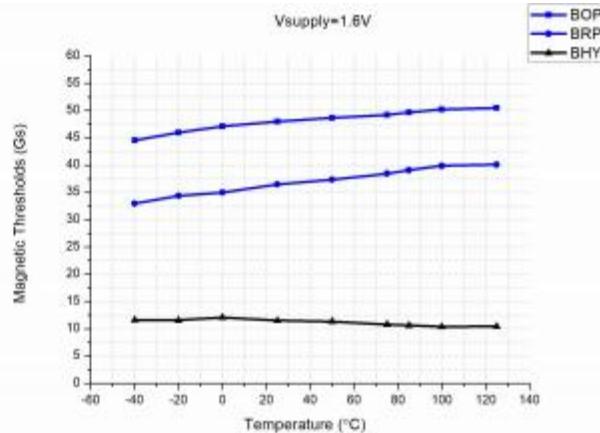
Project	Parameter description	Working conditions	Min	Typ	Max	Unit
SL1613-XL Series						
BOPS	Magnetic field operating point	TA=+25°C , VDD= 1.8V	26	33	38	Gauss
BRPS	Magnetic field release point	TA=+25°C , VDD= 1.8V	16	23	28	
BHY (BOPS - BRPS)	Hysteresis			10		

13. Performance curvegraph

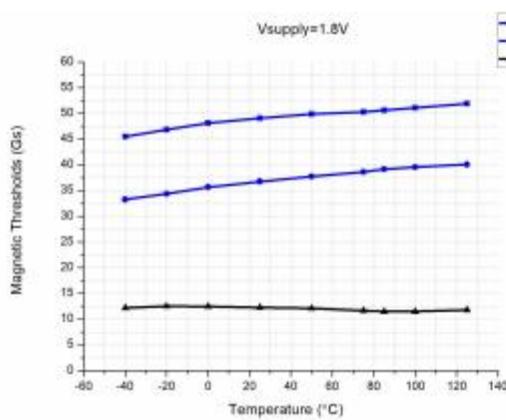
SL1613-XH Series (High threshold version)



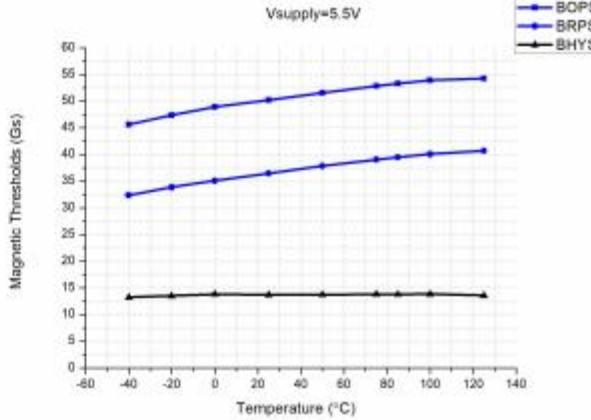
Magnetic field threshold vs Supply voltage @TA=25°C



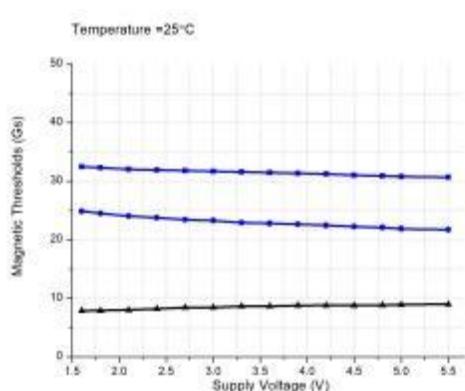
Magnetic field threshold vs Temperature @VDD=1.6



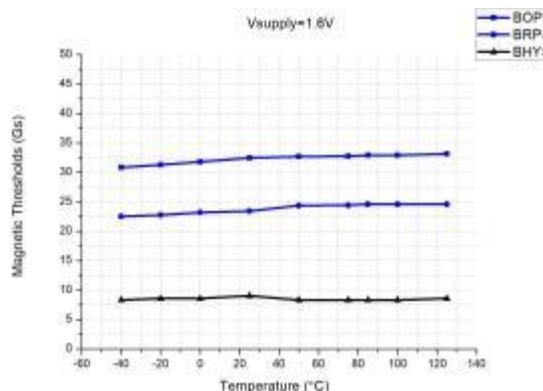
Magnetic field threshold vs Temperature @VDD=1.8V



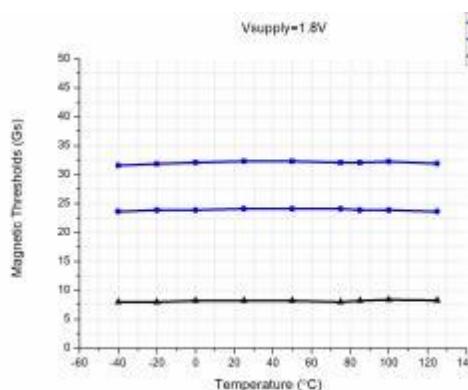
Magnetic field threshold vs Temperature @VDD=5.5

SL1613-XL Series (Low threshold version)

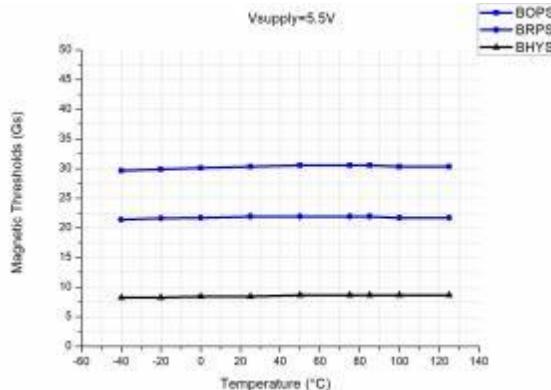
Magnetic field threshold vs Supply voltage @TA=25°C



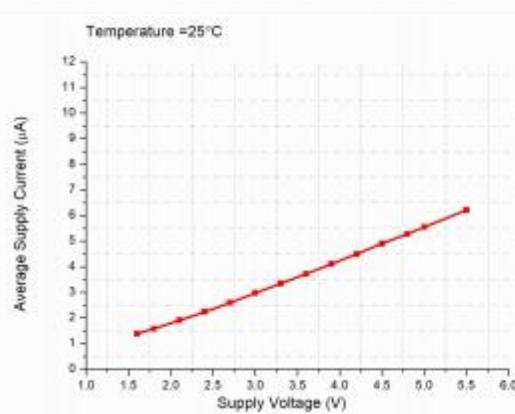
Magnetic field threshold vs Temperature @VDD=1.6



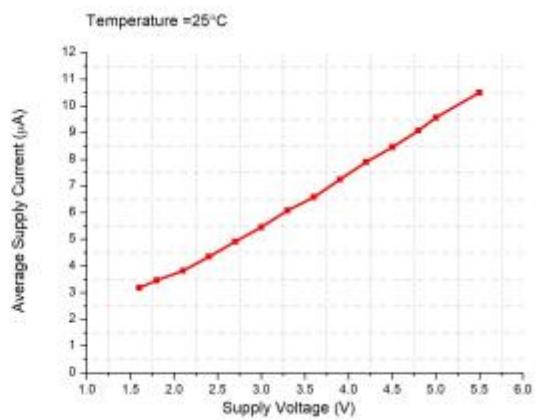
Magnetic field threshold vs Temperature @VDD=1.8V



Magnetic field threshold vs Temperature @VDD=5.5

SL1613-SX Series (Low speed version)

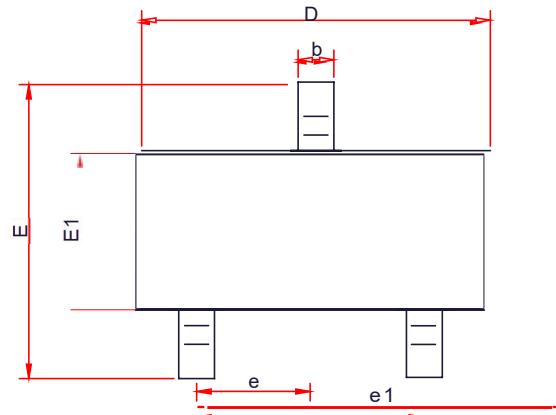
Average operating current vs. Supply voltage @ TA=25°C

SL1613-TX Series(Typical version)

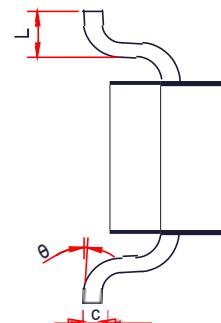
Average operating current vs. Supply voltage @ TA=25°C

14.Ordering Information

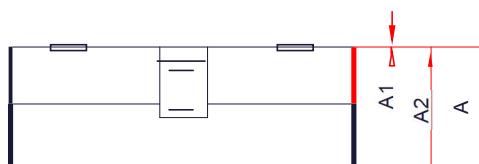
Model	Package	Pin	Magnetic field threshold (Bop)	Switching frequency	Temperature	
SL1613-TH	SOT-23	3	46Gauss	20Hz	-40°C~85°C	
SL1613-TL	SOT-23	3	33Gauss	20Hz	-40°C~85°C	
SL1613-SH	SOT-23	3	46Gauss	5Hz	-40°C~85°C	
SL1613- SL	SOT-23	3	33Gauss	5Hz	-40°C~85°C	

Package Dimensions**SOT-23**

TOP VIEW



SIDE VIEW



SIDE VIEW

Symbol	Dimensions in Millimeters		
	Min.	Typ.	Max.
A	-	-	1.25
A1	0.00	-	0.1
A2	1.00	1.10	1.15
b	0.30	-	0.50
c	0.10	-	0.20
D	2.82	2.95	3.02
E	2.65	2.80	2.95
E1	1.50	1.65	1.70
e	0.85	0.95	1.05
e1	1.80	1.90	2.00
L	0.30	0.45	0.60
θ	0°	-	8°